PCN	Num	ber:	202308	30001.1				PCN Date:			August 31, 2023	
Title		Qualifica	tion of a	ddition	al F	ab Site (RFAB),	Die Rev	/isio	n an	d Asser	nbly BOM options for	
Title	•	select de	evices									
Cust	tomer	Contact:	Chai	ge Ma	nag	ement team	Dept:	: Quality Se			vices	
Prop	posed	1 st Ship	Date:	Nov				nple Requests epted until:			Sept 30, 2023*	
*Sa	mple ı	requests	receive	dafte	r S e	pt 30, 2023 w	/ill not	be s	upp	orted.		
Cha	nge Ty	/pe:										
	Assem	bly Site				Design	Design			Wafer	Bump Material	
	Assem	bly Proces	SS			Data Sheet				Wafer	Bump Process	
\boxtimes	Assem	bly Mater	ials			Part number	change		\boxtimes	Wafer	Fab Site	
						Test Site	Test Site			Wafer Fab Material		
	Packin	g/Shippin	g/Labeli	ıg		Test Process			Wafer	Fab Process		
	·	·				PCN Deta	ils			·		

Description of Change:

Texas Instruments is pleased to announce the qualification of RFAB as an additional wafer fab site, die revision and additional assembly BOM options for the devices listed in the "Product Affected" section.

С	urrent Fab Site	•	Additional Fab Site				
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter		
MIHO	LBC8	200 mm	RFAB	LBC8	300 mm		

The die was also changed as a result of the process change.

Additionally, there will be a BOM options introduced for these devices:

	Current	Proposed
Bond wire diameter	Au, 0.96 mil	0.8 mil Cu
composition, diameter	Au, 0.90 IIIII	0.6 Hill Cu

Reason for Change:

Continuity of supply.

- 1) To align with world technology trends and use wiring with enhanced mechanical and electrical properties
- 2) Maximize flexibility within our Assembly/Test production sites.
- 3) Cu is easier to obtain and stock

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings:

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
No Change	⊠ No Change	☑ No Change	⊠ No Change

Changes to product identification resulting from this PCN:

Fab Site Information:Chip SiteChip Site Origin Code (20L)Chip Site Country Code (21L)Chip Site CityMIHO8MH8JPNIbarakiRFABRFBUSARichardson

Die Rev:

Current	New					
Die Rev [2P]	Die Rev [2P]					
Α	A					

Sample product shipping label (not actual product label)



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483\$I2 (P) (2P) REV: (V) 0033317 (201) 690.5HE (211) CCO.USA (22L) ASO:MLA (23L) ACO:MY\$

.BL: 5A (L)T0:1750

Group 1 Product Affected: Fab site, Assembly BOM (C2212079)

ISO7741BDWR	ISO7741DWR	ISO7741FBDWR	ISO7741FDWR
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Group 2 Product Affected: Fab site, Die Rev, Assembly BOM (C2307066)

ISO7730DWR	ISO7731DWR	ISO7740DWR	ISO7742FDWR
ISO7730FDWR	ISO7731FBDWR	ISO7740FDWR	
ISO7731BDWR	ISO7731FDWR	ISO7742DWR	

Group 1 Qualification Data

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approve Date 20-June-2023

Product Attributes

Attributes	Qual Device:	QBS Reference:	QBS Reference:
Attributes	ISO7741QDWRQ1	UCC23513QDWYQ1	<u>ISO6763QDWRQ1</u>
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Power Management	Interface
Wafer Fab Supplier	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB
Assembly Site	MLA	TAI	MLA
Package Group	SOIC	SOIC	SOIC
Package Designator	DW	DWY	DW
Pin Count	16	6	16

QBS: Qual By Similarity

Qual Device ISO7741QDWRQ1 is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

		Data Disp	olaye	d as	: Number	of lots / T	otal sa	mple size /	Total failed	
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO7741QDWRQ1	QBS Reference: UCC23513QDWYQ1	QBS Reference: ISO6763QDWRQ
Test Group	A - Acc	elerated Environmer	nt Stress	Tests						
PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Preconditioning	MSL2 260C	-	-	No Fails	No Fails
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	3/231/0	3/231/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	3/231/0	3/231/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	3/135/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours	-	3/135/0	-
Test Group B	- Acce	lerated Lifetime Sim	ulation T	ests						
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	-	3/231/0	-
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	-	3/2400/0	-
Test Group C	- Pack	age Assembly Integr	rity Test	s						
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0
SD	C3	JEDEC J-STD- 002	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0	-
SD	C3	JEDEC J-STD- 002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0	-
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0	-
Test Group D) - Die F	abrication Reliability	/ Tests							
ЕМ	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E	E - Elect	rical Verification Tes	ts							
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0	-
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100- 004	-	1/6/0	1/6/0	-
						Cpk>1.67				

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420

The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C Grade 1 (or Q): -40C to +125C Grade 2 (or T): -40C to +105C Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

Room/Hot: THB/HAST, TC/PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Quality and Environmental data is available at Tl's external Web site: http://www.ti.com/

Group 2 Qualification Data

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approve Date 15-August-2023

Product Attributes

Attributes	Qual Device:	Qual Device:	QBS Reference:	QBS Reference:	QBS Reference:
Attributes	IS07742QDWRQ1	ISO7740QDWRQ1	UCC23513QDWYQ1	ISO6763QDWRQ1	IS07741QDWRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Interface	Power Management	Interface	Interface
Wafer Fab Supplier	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB
Assembly Site	MLA	MLA	TAI	MLA	MLA
Package Group	SOIC	SOIC	SOIC	SOIC	SOIC
Package Designator	DW	DW	DWY	DW	DW
Pin Count	16	16	6	16	16

QBS: Qual By Similarity

Qual Device ISO7742QDWRQ1 is qualified at MSL2 260C

Qual Device ISO7740QDWRQ1 is qualified at MSL2 260C

Qual Device ISO7730QDWRQ1 is qualified at MSL2 260C

Qual Device ISO7731QDWRQ1 is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO7742QDWRQ1	Qual Device: ISO7740QDWRQ1	QBS Reference: UCC23513QDWYQ1	QBS Reference: ISO6763QDWRQ1	QBS Reference: ISO7741QDWRQ1
Test Group	st Group A - Accelerated Environment Stress Tests											
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C	-	-	-	No Fails	No Fails	-
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours			3/231/0	3/231/0	
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	-	-	3/231/0	3/231/0	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	3/231/0	3/231/0	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	-	3/135/0	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-	3/135/0	-	-

Test Group	B - Acce	elerated Lifetime	e Simula	tion Tes	ts							
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	-	-	3/231/0	-	-
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours	-	-	3/2400/0	-	-
Test Group	C - Pack	age Assembly	Integrity	Tests					•			
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-	3/90/0	3/90/0	1/30/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-	3/90/0	3/90/0	1/30/0
SD	С3	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	1/15/0	-	-
SD	C3	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	1/15/0	-	-
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-	-	3/30/0	-	1/10/0
Test Group	D - Die F	abrication Reli	ability Te	sts								
ЕМ	D1	JESD61			Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28			Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-		-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-			Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	E - Elect	trical Verificatio	n Tests									
ESD	E2	AEC Q100- 002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0	1/3/0	-	1/3/0
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0	1/3/0	-	1/3/0
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	1/6/0	1/6/0	-	1/6/0
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	1/30/0	3/90/0	3/90/0	1/30/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C Grade 1 (or Q): -40C to +125C Grade 2 (or T): -40C to +105C Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

Room/Hot: THB/HAST, TC/PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

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